# SMF05CT1G, SMF12CT1G, SMF15CT1G, SMF24CT1G, SZSMF12CT1G

# **ESD Protection Diode Array,** 5-Line

This 5-line surge protection array is designed for application requiring transient voltage protection capability. It is intended for use in over-transient voltage and ESD sensitive equipment such as computers, printers, automotive electronics, networking communication and other applications. This device features a monolithic common anode design which protects five independent lines in a single SC-88 package.

#### Features

- Protects up to 5-Line in a Single SC-88 Package
- Peak Power Dissipation 100 W (8 x 20 µs Waveform)
- ESD Rating of Class 3B (Exceeding 8 kV) per Human Body Model and Class C (Exceeding 400 V) per Machine Model.
- Compliance with IEC 61000–4–2 (ESD) 15 kV (Air), 8 kV (Contact)
- Flammability Rating of UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- Pb-Free Packages are Available\*

#### Applications

- Hand-Held Portable Applications
- Networking and Telecom
- Automotive Electronics
- Serial and Parallel Ports
- Notebooks, Desktops, Servers

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Rating	Value	Unit
P <sub>PK</sub> 1	Peak Power Dissipation 8 x 20 µs Double Exponential Waveform (Note 1)	100	W
TJ	Operating Junction Temperature Range	-40 to 125	°C
T <sub>STG</sub>	Storage Temperature Range	–55 to 150	°C
ΤL	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body Model (HBM) Machine Model (MM) IEC 61000-4-2 Air (ESD) IEC 61000-4-2 Contact (ESD)	16000 400 15000 15000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Nonrepetitive current pulse per Figure 3.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



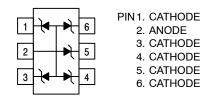
## **ON Semiconductor®**

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## SC-88 FIVE SURGE PROTECTION 100 W PEAK POWER

SC-88 CASE 419B STYLE 24

### **PIN ASSIGNMENT**



### MARKING DIAGRAM



XX = Specific Device Code 6J = SMF05C 6K = SZSMF12C/SMF12C 6L = SMF15C 6M = SMF24C M = Date Code - Ph. Free Package

#### = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

# SMF05CT1G, SMF12CT1G, SMF15CT1G, SMF24CT1G, SZSMF12CT1G

#### SMF05CT1G ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = $25^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	(Note 2)			5.0	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> = 1 mA, (Note 3)	6.2		7.2	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 5 V		0.07	5.0	μΑ
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 5 A (8 x 20 μs Waveform)			9.8	V
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 8 A (8 x 20 μs Waveform)			12.5	V
Maximum Peak Pulse Current	I <sub>PP</sub>	8 x 20 μs Waveform			8.0	Α
Capacitance	CJ	V <sub>R</sub> = 0 V, f = 1 MHz (Line to GND)		80	130	pF

### SMF12CT1G ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	(Note 2)			12	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> = 1 mA, (Note 3)	13.3		15	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 12 V		0.01	0.1	μA
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 3 A (8 x 20 μs Waveform)			21	V
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 6 A (8 x 20 μs Waveform)			23	V
Maximum Peak Pulse Current	I <sub>PP</sub>	8 x 20 μs Waveform			6.0	А
Capacitance	CJ	$V_R = 0 V$ , f = 1 MHz (Line to GND)		40	60	pF

#### SMF15CT1G ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = $25^{\circ}$ C, unless otherwise specified)

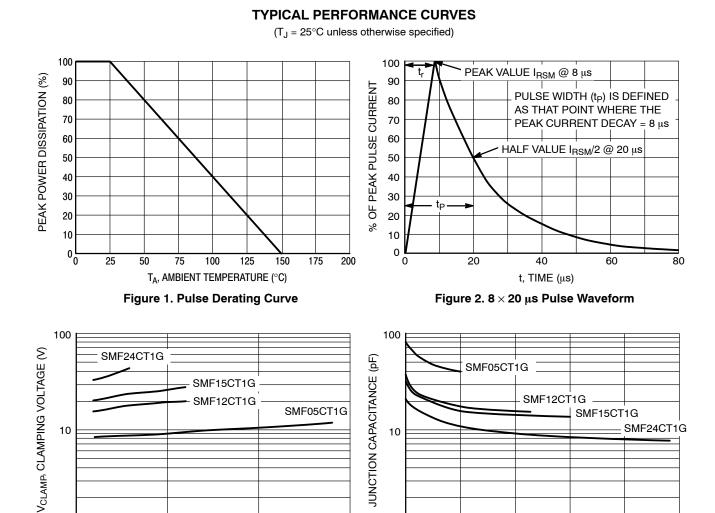
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	(Note 2)			15	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> = 1 mA, (Note 3)	17		19	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 15 V		0.01	1.0	μA
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 1 A (8 x 20 μs Waveform)			23	V
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 5 A (8 x 20 μs Waveform)			29	V
Maximum Peak Pulse Current	I <sub>PP</sub>	8 x 20 μs Waveform			5.0	А
Capacitance	CJ	V <sub>R</sub> = 0 V, f = 1 MHz (Line to GND)		33	45	pF

### SMF24CT1G ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = $25^{\circ}$ C, unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	(Note 2)			24	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> = 1 mA, (Note 3)	26.7		32	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 24 V		0.01	1.0	μA
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 1 A (8 x 20 μs Waveform)			40	V
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 2.5 A (8 x 20 μs Waveform)			44	V
Maximum Peak Pulse Current	I <sub>PP</sub>	8 x 20 μs Waveform			2.5	Α
Capacitance	CJ	V <sub>R</sub> = 0 V, f = 1 MHz (Line to GND)		21	25	pF

2. Surge protection devices are normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal or greater than the DC or continuous peak operating voltage level. 3.  $V_{BR}$  is measured at pulse test current I<sub>T</sub>. 4. Include SZ-prefix devices where applicable.

## SMF05CT1G, SMF12CT1G, SMF15CT1G, SMF24CT1G, SZSMF12CT1G



#### **ORDERING INFORMATION**

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0

Device	Package	Shipping <sup>†</sup>
SMF05CT1G	SC-88 (Pb-Free)	3,000 / Tape & Reel
SMF05CT2G*	SC-88 (Pb-Free)	3,000 / Tape & Reel
SMF12CT1G	SC-88 (Pb-Free)	3,000 / Tape & Reel
SMF15CT1G	SC-88 (Pb-Free)	3,000 / Tape & Reel
SMF24CT1G	SC-88 (Pb-Free)	3,000 / Tape & Reel

1

15

0

5

10

V<sub>BR</sub>, REVERSE VOLTAGE (V)

Figure 4. Junction Capacitance vs Reverse Voltage

20

25

15

10

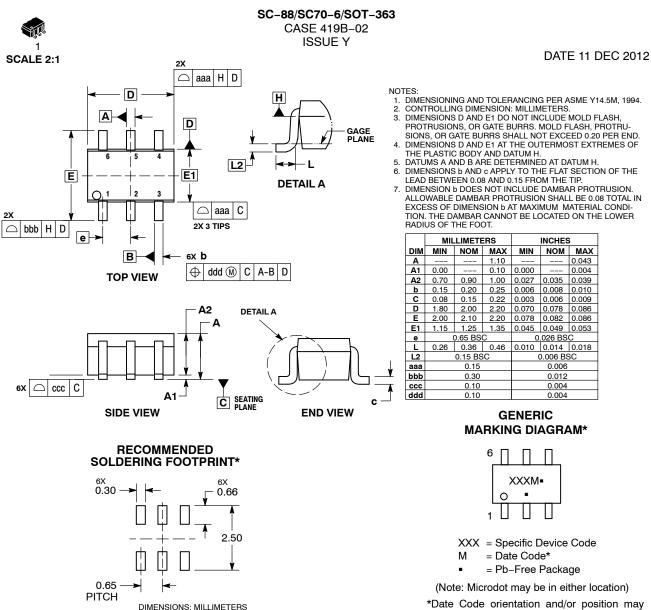
IPP, PEAK PULSE CURRENT (A)

Figure 3. Clamping Voltage vs Peak Pulse Current

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*The "T2" suffix refers to an alternate tape & reel orientation.





- \*Date Code orientation and/or position may vary depending upon manufacturing location.
  - \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

## **STYLES ON PAGE 2**

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\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and

Mounting Techniques Reference Manual, SOLDERRM/D.

#### SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

### DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

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